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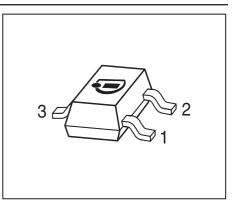


BCX41

NPN Silicon AF and Switching Transistor

- For general AF applications
- High breakdown voltage
- Low collector-emitter saturation voltage
- Complementary type: BCX42 (PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101





Туре	Marking	Pin Configuration			Package
BCX41	EKs	1 = B	2 = E	3 = C	SOT23

Maximum Ratings

Junction - soldering point¹⁾

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V _{CEO}	125	V	
Collector-base voltage	V _{CBO}	125		
Emitter-base voltage	V _{EBO}	5		
Collector current	I _C	800	mA	
Peak collector current, $t_p \le 10 \text{ ms}$	I _{CM}	1	A	
Base current	I _B	100	mA	
Peak base current	/ _{BM}	200		
Total power dissipation	P _{tot}	330	mW	
<i>T</i> _S ≤ 79 °C				
Junction temperature	Ti	150	°C	
Storage temperature	T _{stg}	-65 150		
Thermal Resistance				
Parameter	Symbol	Value	Unit	

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

K/W

≤ 215

R_{thJS}



Electrical Characteristics at <i>T</i> _A = 25°C, ur Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics			1	İ	1
Collector-emitter breakdown voltage	V _{(BR)CEO}	125	-	-	V
$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 0					
Collector-base breakdown voltage	V _{(BR)CBO}	125	-	-	
$I_{\rm C}$ = 100 µA, $I_{\rm E}$ = 0					
Emitter-base breakdown voltage	V _{(BR)EBO}	5	-	-	
$I_{\rm E}$ = 10 µA, $I_{\rm C}$ = 0					
Collector-base cutoff current	I _{CBO}				μA
$V_{\rm CB} = 100 \text{ V}, I_{\rm E} = 0$		-	-	0.1	
$V_{\rm CB} = 100 \text{ V}, I_{\rm E} = 0 \text{ , } T_{\rm A} = 150 ^{\circ}{\rm C}$		-	-	20	
Collector-emitter cutoff current	I _{CEO}				
V _{CE} = 100 V, <i>T</i> _A = 85 °C		-	-	10	
V _{CE} = 100 V, <i>T</i> _A = 125 °C		-	-	75	
Emitter-base cutoff current	I _{EBO}	-	-	100	nA
$V_{\rm EB} = 4 \text{V}, I_{\rm C} = 0$					
DC current gain ¹⁾	h _{FE}				-
$I_{\rm C}$ = 100 µA, $V_{\rm CE}$ = 1 V		25	-	-	
<i>I</i> _C = 100 mA, <i>V</i> _{CE} = 1 V		63	-	-	
$I_{\rm C}$ = 200 mA, $V_{\rm CE}$ = 1 V		40	-	-	
Collector-emitter saturation voltage ¹⁾	V _{CEsat}	-	-	0.9	V
/ _C = 300 mA, / _B = 30 mA					
Base emitter saturation voltage ¹⁾	V _{BEsat}	-	-	1.4	
<i>I</i> _C = 300 mA, <i>I</i> _B = 30 mA					
AC Characteristics					
Transition frequency	f _T	-	100	-	MHz
$I_{\rm C}$ = 20 mA, $V_{\rm CE}$ = 5 V, f = 20 MHz					
Collector-base capacitance	C _{cb}	-	12	-	pF
V _{CB} = 10 V, <i>f</i> = 1 MHz					
	1			•	

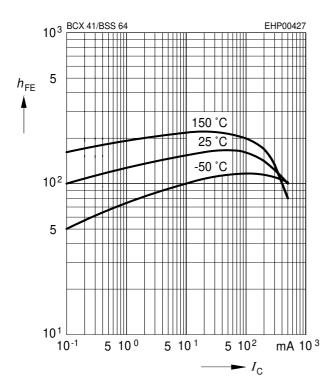
Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

¹Pulse test: t < 300 μ s; D < 2%



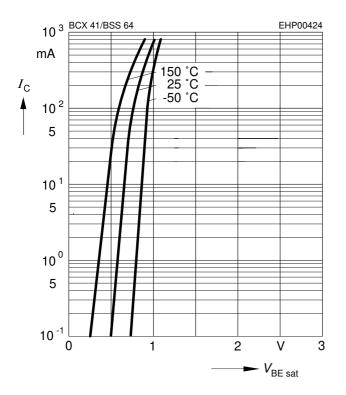
DC current gain $h_{\text{FE}} = f(I_{\text{C}})$

 $V_{CE} = 1 V$



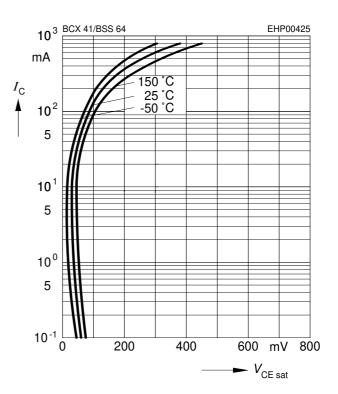
Base-emitter saturation voltage

 $I_{\rm C} = f(V_{\rm BEsat}), h_{\rm FE} = 10$

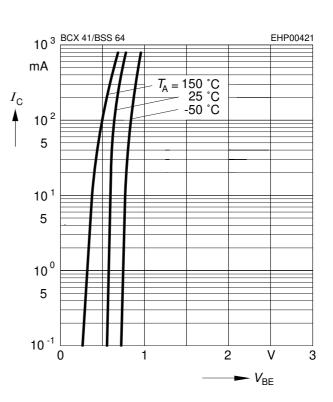


Collector-emitter saturation voltage

 $I_{\rm C} = f(V_{\rm CEsat}), h_{\rm FE} = 10$

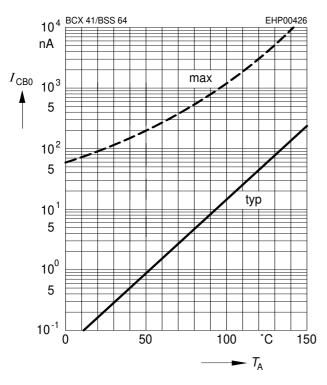


Collector current $I_{\rm C} = f(V_{\rm BE})$ $V_{\rm CE} = 1V$

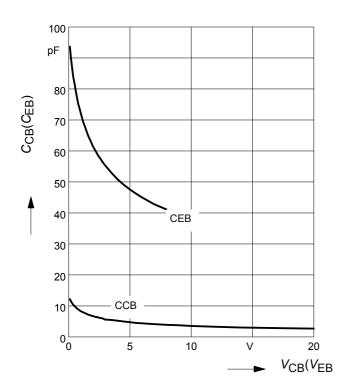




 $V_{\rm CBO}$ = 80 V

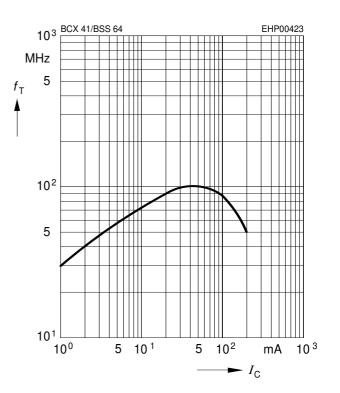


Collector-base capacitance $C_{cb} = f(V_{CB})$ Emitter-base capacitance $C_{eb} = f(V_{EB})$

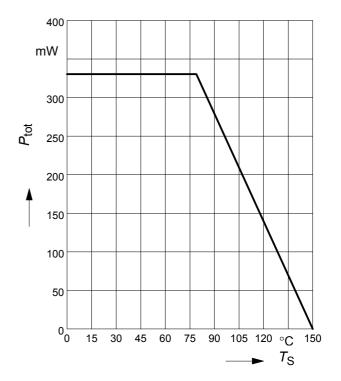


Transition frequency $f_{\rm T} = f(I_{\rm C})$

 V_{CE} = 5 V



Total power dissipation $P_{tot} = f(T_S)$

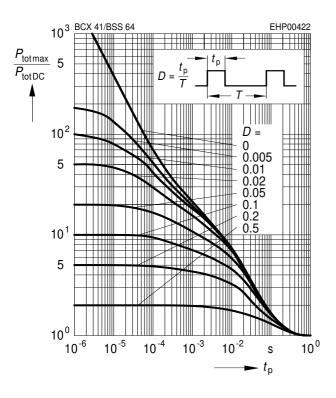




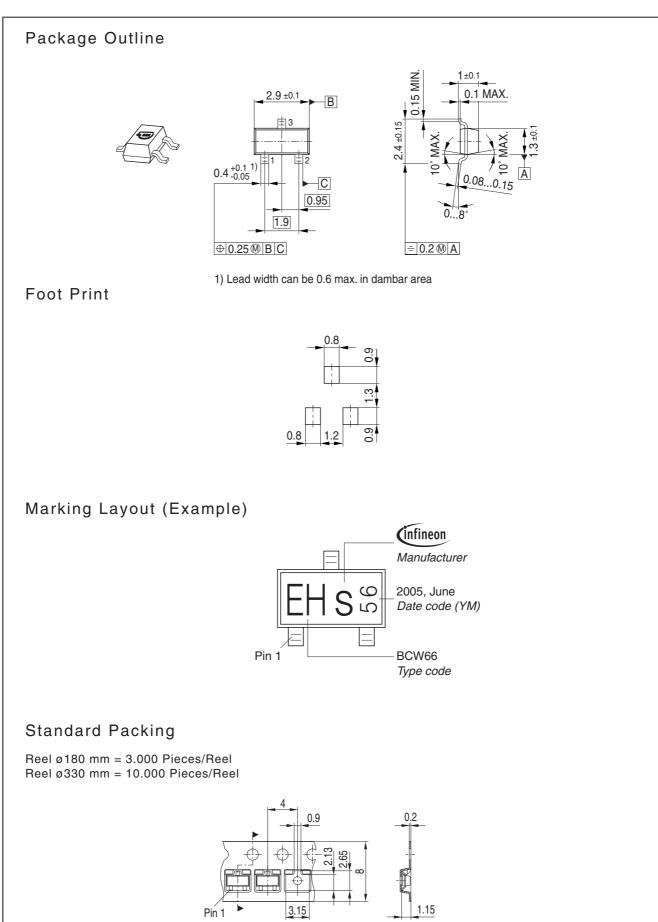
BCX41

Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$









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